

**P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Product Summary**

<b>BV<sub>DSS</sub></b>	<b>R<sub>DS(ON)</sub></b>	<b>I<sub>D</sub></b> <b>T<sub>A</sub> = +25°C</b>
-50V	10Ω @ V <sub>GS</sub> = -5V	-130mA

**Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

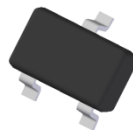
**Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

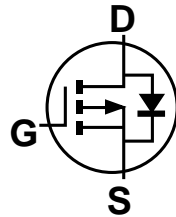
**Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208 Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe). **Ⓒ3**
- Weight: 0.006 grams (Approximate)

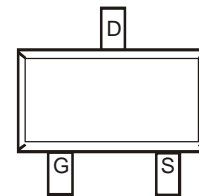
SOT323



Top View



Equivalent Circuit



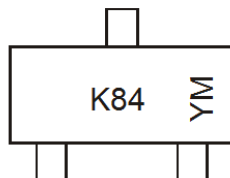
Top View

**Ordering Information** (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
BSS84W-7-F	Standard	SOT323	3000 / Tape & Reel
BSS84WQ-7-F	Automotive	SOT323	3000 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to <https://www.diodes.com/quality/>.
  5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



K84 = Product Type Marking Code  
 YM or  $\overline{Y}M$  = Date Code Marking  
 Y or  $\overline{Y}$  = Year (ex: G = 2019)  
 M = Month (ex: 9 = September)

Shanghai A/T Site

Date Code Key

Year	2012	~	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	Z	~	G	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-50	V
Drain-Gate Voltage (Note 6)	V <sub>DGR</sub>	-50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 6)	I <sub>D</sub>	-130	mA
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-1	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50	-75	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
		—	—	-2	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C
		—	—	-100	nA	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.8	-1.6	-2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	6	10	Ω	V <sub>GS</sub> = -5V, I <sub>D</sub> = -0.1A
Forward Transconductance	g <sub>FS</sub>	0.05	—	—	S	V <sub>DS</sub> = -25V, I <sub>D</sub> = -0.1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	—	45	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	12	pF	
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	10	—	ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A, R <sub>GEN</sub> = 50Ω, V <sub>GS</sub> = -10V
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	18	—	ns	

- Notes:
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Incorporated's suggested pad layout document, which can be found on our website at <http://www.diodes.com/package-outlines.html>.
  - Short duration pulse test used to minimize self-heating effect.
  - Guarantee by design. Not subject to production testing.

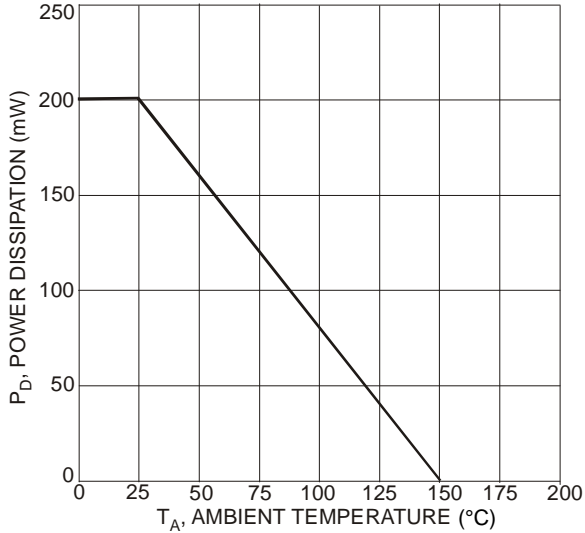


Fig. 1 Max Power Dissipation vs. Ambient Temperature

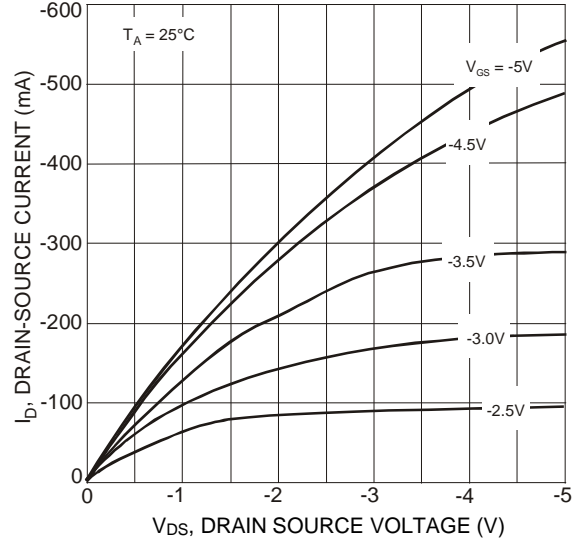


Fig. 2 Drain Source Current vs. Drain Source Voltage

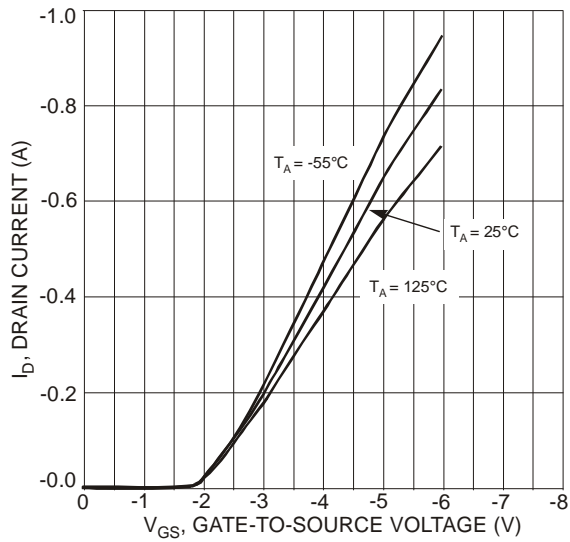


Fig. 3 Drain Current vs. Gate Source Voltage

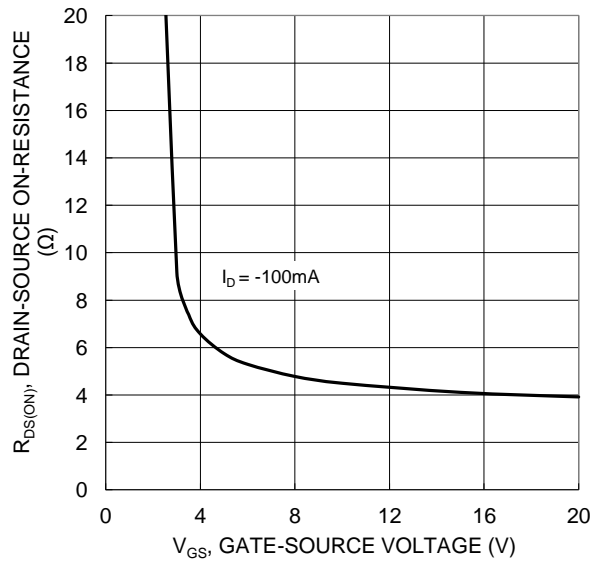


Fig. 4 Typical Transfer Characteristic

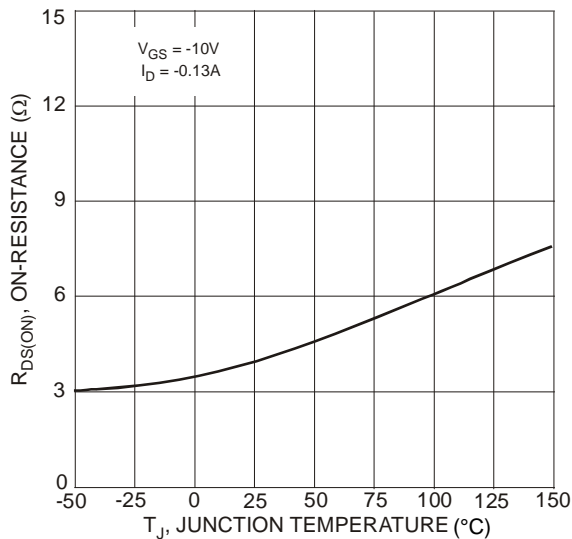


Fig. 5 On-Resistance vs. Junction Temperature

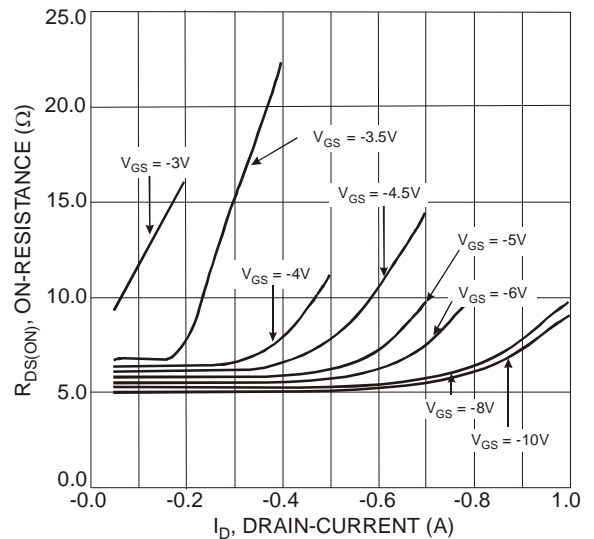
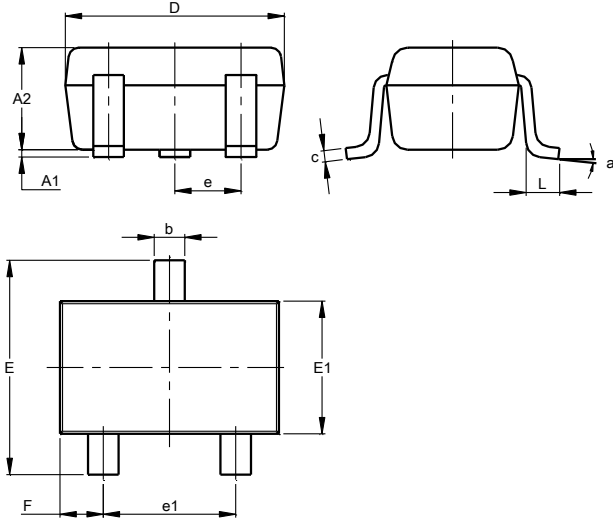


Fig. 6 On-Resistance vs. Drain-Current

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT323**

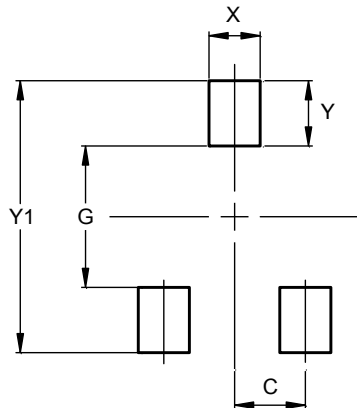


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT323**



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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